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Patent

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Paul JANKE) Re: Information Disclosure
) Statement
Serial No.: 10/797,202) Group: not yet assigned
)
Filed: March 9, 2004) Examiner: not yet assigned
)
For: "A METHOD OF FORMING A) Our Ref: B-4127NP 621599-6
STRUCTURE...")
) Date: August 10, 2004

Commissioner for Patents
P.O. Box 1450
Alexandria VA, 22313-1450

Sir:

In accordance with the Applicant's duty to disclose information which may be material to the examination of this application, the undersigned respectfully requests that the Examiner consider on the merits the documents listed on the enclosed Form PTO-1449 (modified) before issuing the first Office Action on the merits. Copies of the foreign patent documents and the non-patent publications listed on the enclosed Form PTO-1449 (modified) are enclosed herewith for the Examiner's convenience. Copies of the U.S. patent documents listed on the enclosed Form PTO-1449 (modified) are not enclosed, pursuant to Deputy Commissioner Stephen G. Kunin's Pre OG Notice dated July 11, 2003.

The filing of this Information Disclosure Statement (IDS) shall not be construed as a representation that a search has been made (37 C.F.R. 1.97(g)), an admission that the information cited is, or is considered to be, material to patentability, or that no other material information exists.

The Applicant believes that this IDS is being submitted before the issuance of a first Office Action on the merits and before the issuance of a Final Rejection or Notice of Allowance. Therefore, no official fees should be due; and this IDS should be considered


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on the merits. If this IDS is being submitted after the issuance of the first Office Action on the merits and before the issuance of a Final Rejection or Notice of Allowance, please contact the undersigned to authorize a payment of \$180.00 (or any other required amount), which is the fee set forth in 37 C.F.R. § 1.97(c), if the Examiner believes that such a fee is due in order for this IDS to be considered on the merits.

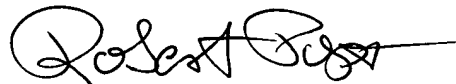
The filing of this Information Disclosure Statement shall not be construed as an admission against interest in any manner. (Notice of January 9, 1992, 1135 O.G. 13-25, at 25.)

The person making this statement is the practitioner who signs below on the basis of information supplied by an individual associated with the filing and prosecution of this application (37 C.F.R. § 1.56(c)) and on the basis of information in the practitioner's file.

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first-class mail in an envelope addressed to the "Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450", on August 10, 2004 by Shana Morda.



Respectfully submitted,



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Enclosures: Form PTO-1449 (modified) (1 page)
Copy of Non-U.S. Patent documents listed on Form PTO-1449 (modified)



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Form PTO-1449 (Modified)	ATTY DOCKET NO. B-4127NP 621599-6	U.S. SERIAL NO. 10/797,202
LIST OF PATENTS AND PUBLICATIONS STATEMENT	APPLICANTS Paul JANKE	
	FILING DATE March 9, 2004	GROUP not yet assigned

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	ISSUE DATE	NAME	CLASS	SUB- CLASS	FILING DATE or 102(e) DATE IF APPROPRIATE
	5,739,557	4/1998	O'Neil II et al.	257	192	

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	Suemitsu, T., et al., "Improved Recessed-Gate Structure For Sub-0.1- μ m-Gate InP-Based High Electron Mobility Transistors," <i>Jpn. J. Appl. Phys.</i> , Vol. 37, Part 1, No. 3B, pp. 1365-1372 (March 1998).
	Tanenbaum, D.M., et al., "High Resolution Electron Beam Lithography Using ZEP-520 and KRS Resists At Low Voltage," <i>J. Vac. Sci. Technol. B</i> , Vol. 14, No. 6, pp. 3829-3833 (Nov/Dec 1996).
	"ZEP Series: Positive Tone, Chemically Amplified Type For Device Fabrication," <i>Zeon Corporation</i> INTERNET: < http://www.zeon.co.jp/products/imagelec2c2.html > 1 page total (2002).
	"ZEP520" <i>Zeon Corporation</i> INTERNET: < http://www.zeon.co.jp/ > Version 1.02, pp. 1-11 (March 2001).

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.